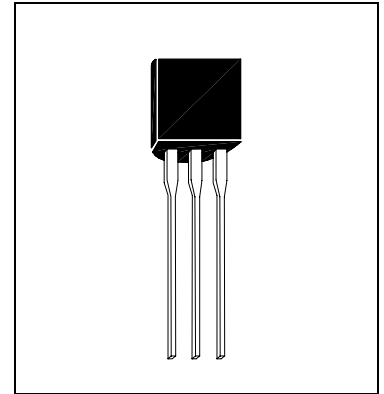




2N6517

NPN EPITAXIAL PLANAR TRANSISTOR



Description

The 2N6517 is designed for general purpose applications requiring high breakdown voltages.

Features

- High Collector-Emitter Breakdown Voltage.
- Low Collector-Emitter Saturation Voltage.
- The 2N6517 is complementary to 2N6520.

Absolute Maximum Ratings

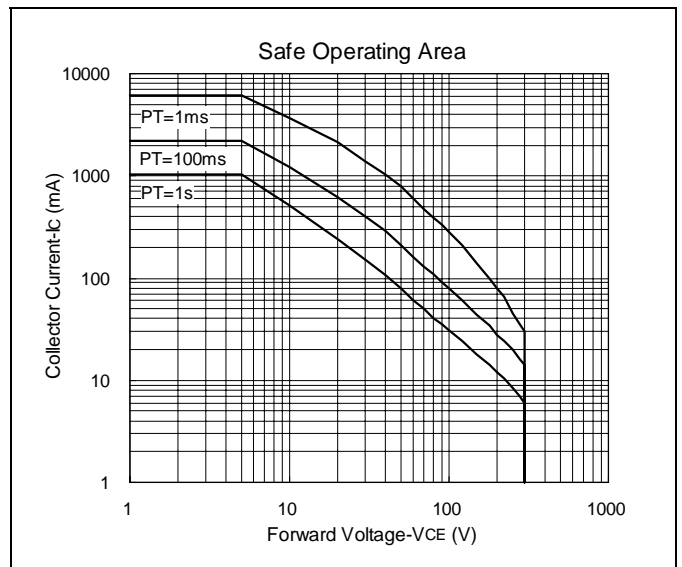
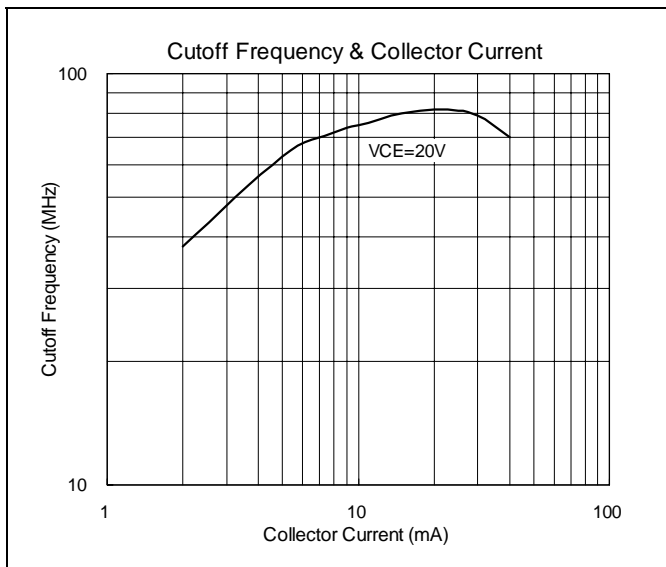
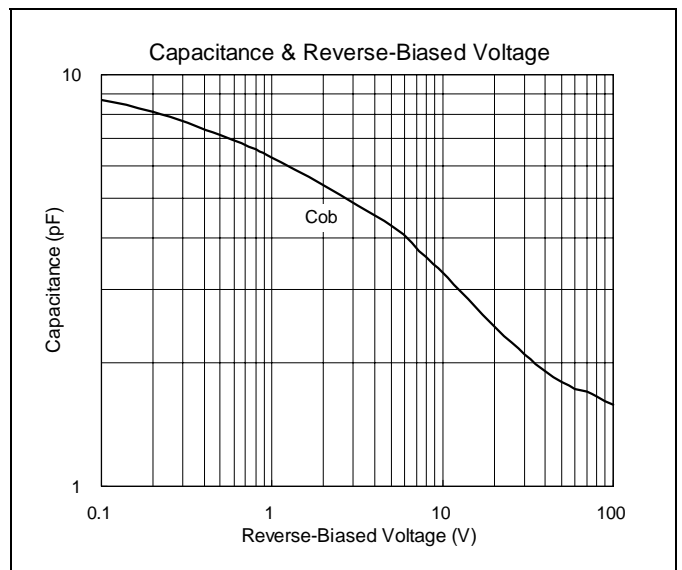
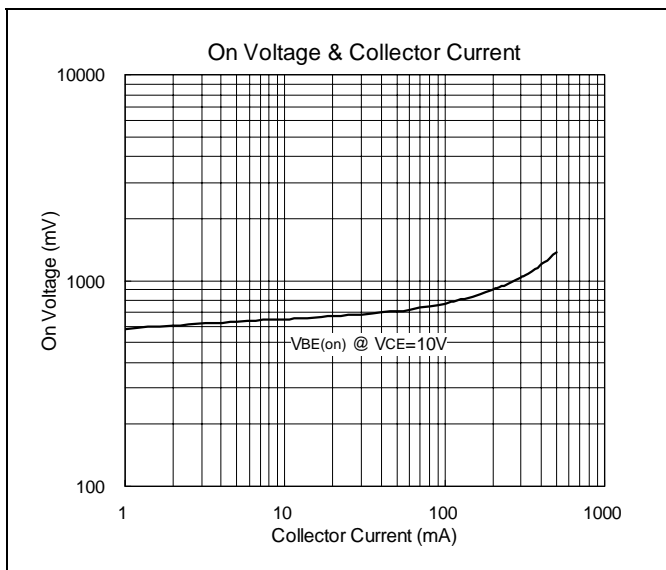
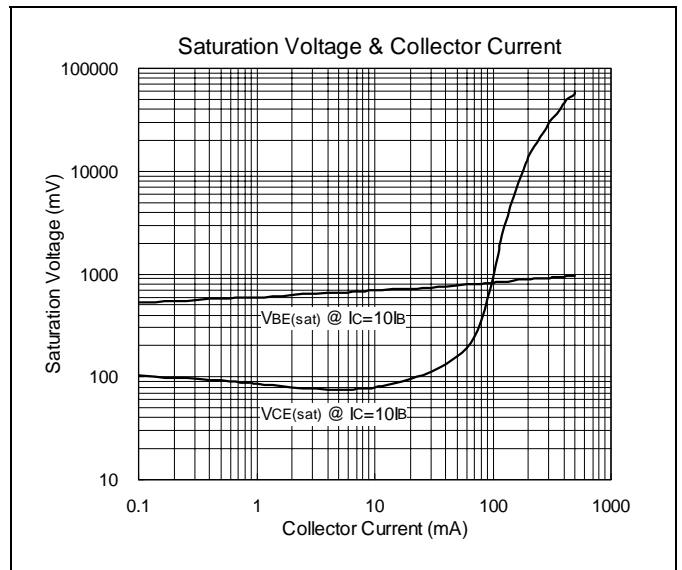
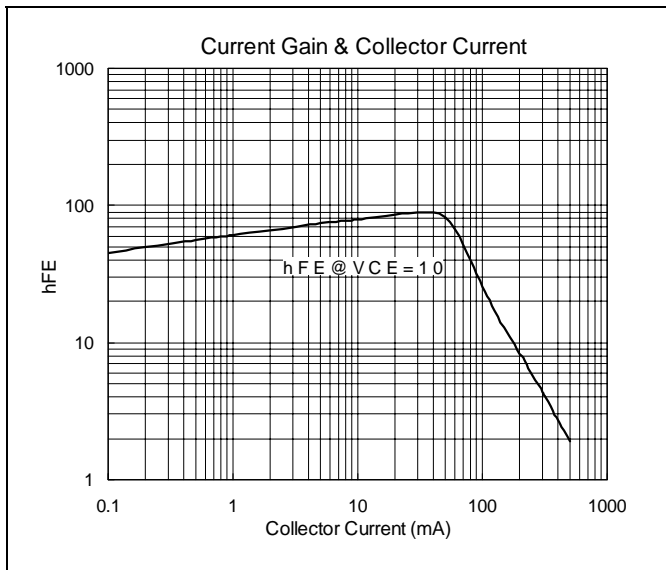
- Maximum Temperatures
 - Storage Temperature -55~+150°C
 - Junction Temperature +150°C Maximum
- Maximum Power Dissipation
 - Total Power Dissipation (Ta=25°C)..... 625 mW
- Maximum Voltages and Currents (Ta=25°C)
 - VCBO Collector to Base Voltage..... 350 V
 - VCEO Collector to Emitter Voltage..... 350 V
 - VEBO Emitter to Base Voltage..... 5 V
 - IC Collector Current 500 mA
 - IB Base Current 250 mA

Characteristics (Ta=25°C)

Symbol	Min.	Typ.	Max.	Unit	Test Conditions
BVCBO	350	-	-	V	IC=100uA, IE=0
BVCEO	350	-	-	V	IC=1mA, IB=0
BVEBO	5	-	-	V	IE=10uA, IC=0
ICBO	-	-	50	nA	VCB=250V, IE=0
IEBO	-	-	50	nA	VEB=5V, IC=0
VCE(sat)1	-	-	0.30	V	IC=10mA, IB=1mA
VCE(sat)2	-	-	0.35	V	IC=20mA, IB=2mA
VCE(sat)3	-	-	0.50	V	IC=30mA, IB=3mA
VCE(sat)4	-	-	1.00	V	IC=50mA, IB=5mA
VBE(on)	-	-	2	V	IC=100mA, VCE=10V
VBE(sat)1	-	-	0.75	V	IC=10mA, IB=1mA
VBE(sat)2	-	-	0.85	V	IC=20mA, IB=2mA
VBE(sat)3	-	-	0.90	V	IC=30mA, IB=3mA
hFE1	20	-	-		VCE=10V, IC=1mA
hFE2	30	-	-		VCE=10V, IC=10m
hFE3	30	-	200		VCE=10V, IC=30mA
hFE4	20	-	200		VCE=10V, IC=50mA
hFE5	15	-	-		VCE=10V, IC=100mA
fT	40	-	200	MHz	IC=10mA, VCE=20V, f=20MHz
Cob	-	-	6	pF	VCB=20V, f=1MHz, IE=0

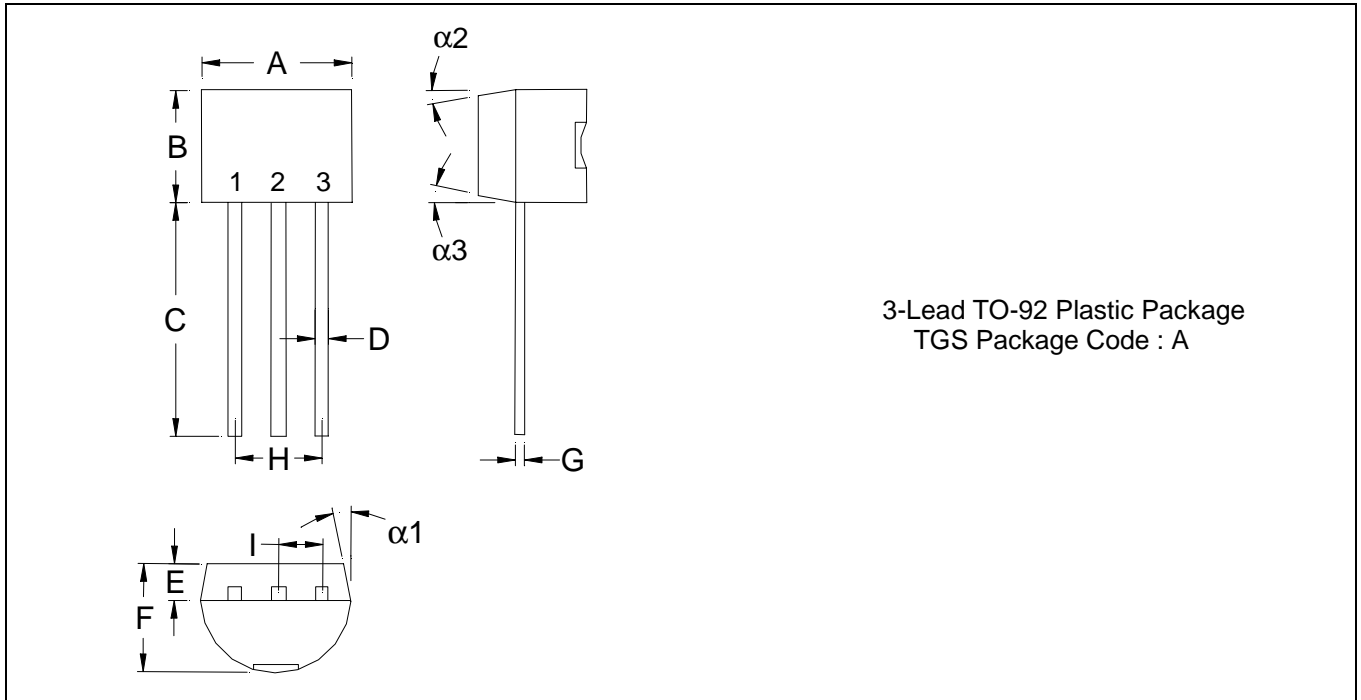


Characteristics Curve





TO-92 Dimension



*:Typical

DIM	Inches		Millimeters		DIM	Inches		Millimeters	
	Min.	Max.	Min.	Max.		Min.	Max.	Min.	Max.
A	0.1704	0.1902	4.33	4.83	G	0.0142	0.0220	0.36	0.56
B	0.1704	0.1902	4.33	4.83	H	-	*0.1000	-	*2.54
C	0.5000	-	12.70	-	I	-	*0.0500	-	*1.27
D	0.0142	0.0220	0.36	0.56	$\alpha 1$	-	*5°	-	*5°
E	-	*0.0500	-	*1.27	$\alpha 2$	-	*2°	-	*2°
F	0.1323	0.1480	3.36	3.76	$\alpha 3$	-	*2°	-	*2°